

#### **Features**

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- Moisture Sensitivity Level 1
- · Halogen Free Available Upon Request By Adding Suffix "-HF"
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

Operating Junction Temperature Range : -55°C to +150°C

• Storage Temperature Range: -55°C to +150°C

• Thermal Resistance: 20°C/W Junction to Ambient

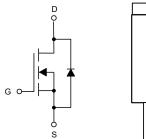
• Thermal Resistance: 2.5°C/W Junction to Case

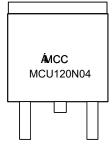
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Volltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	120	Α
Pulsed Drain Current <sup>(1)</sup>	I <sub>DM</sub>	390	Α
Total Power Dissipation <sup>(2)</sup>	P <sub>D</sub>	110	W
Single Pulsed Avalanche Energy <sup>(3)</sup>	E <sub>AS</sub>	272	mJ

#### Note:

- 1. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.
- 2. The power dissipation  $P_D$  is based on  $T_{J(MAX)}$ =150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- 3.  $T_J=25$ °C,  $V_{DD}=40$ V,  $V_{G}=10$ V, L=0.5mH.

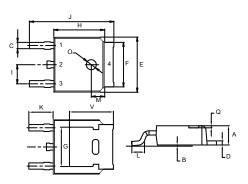
# ±bh/fbU Ghfi Wi fY and Marking Code





# N-CHANNEL MOSFET





- 1. Gate
- 2,4. Drain
  - 3. Source

DIMENSIONS						
DIM	INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.087	0.094	2.20	2.40		
В	0.000	0.005	0.00	0.13		
С	0.026	0.034	0.66	0.86		
D	0.018	0.023	0.46	0.58		
Е	0.256	0.264	6.50	6.70		
F	0.201	0.215	5.10	5.46		
G	0.190		4.83		TYP.	
Н	0.236	0.244	6.00	6.20		
I	0.086	0.094	2.18	2.39		
J	0.386	0.409	9.80	10.40		
K	0.114		2.90		TYP.	
L	0.055	0.067	1.40	1.70		
M	0.063		1.60		TYP.	
0	0.043	0.051	1.10	1.30		
Q	0.000	0.012	0.00	0.30		
V	V 0.211		5.3	35	TYP.	

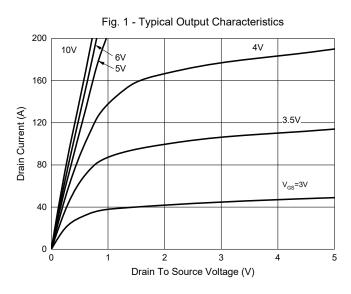


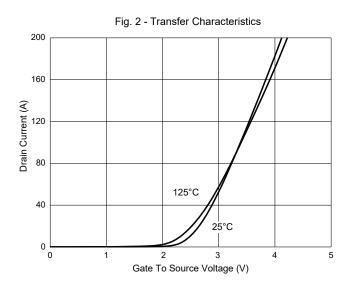
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

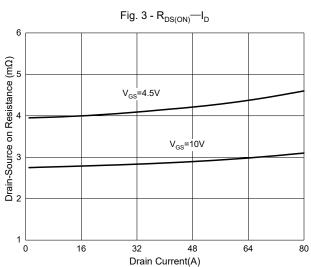
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics	<u>'</u>			1		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40			V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V			1	μA
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	1	1.5	2.5	V
Drain-Source On-Resistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =15A		2.8	3.5	mΩ
Drain-Source On-Resistance	$R_{DS(on)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		4	4.8	mΩ
Gate Resistance	$R_g$	f=1MHz, Open drain		3.1		Ω
Diode Characteristics	•		•	•		
Continuous Body Diode Current	Is				120	Α
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	L 004 H / H 4004 /		22.3		ns
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =20A, dI <sub>F</sub> /dt=100A/μs		7.4		nC
Dynamic Characteristics	•		•	•		
Input Capacitance	C <sub>iss</sub>			4645		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V,f=1MHz		436		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			360		
Total Gate Charge	Qg			102		
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =20V,V <sub>GS</sub> =10V,I <sub>D</sub> =20A		15.8		nC
Gate-Drain Charge	$Q_{gd}$			21.9		
Turn-On Delay Time	t <sub>d(on)</sub>			12		
Turn-On Rise Time	t <sub>r</sub>	V <sub>DS</sub> =20V, V <sub>GEN</sub> =10V,		54		no
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G=3\Omega$ , $I_{DS}=20A$		120		ns
Turn-Off Fall Time	t <sub>f</sub>			80		

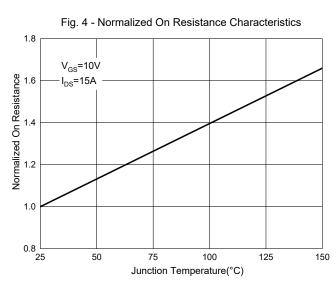


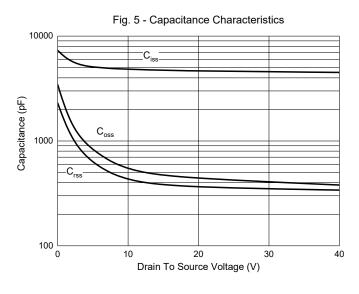
## **Curve Characteristics**

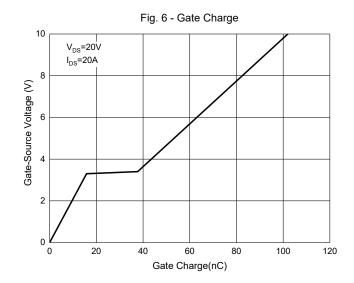














## **Curve Characteristics**

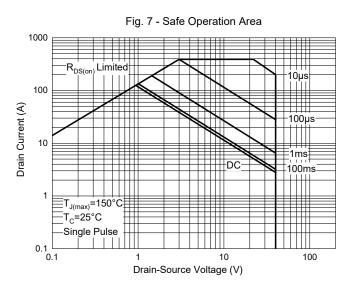
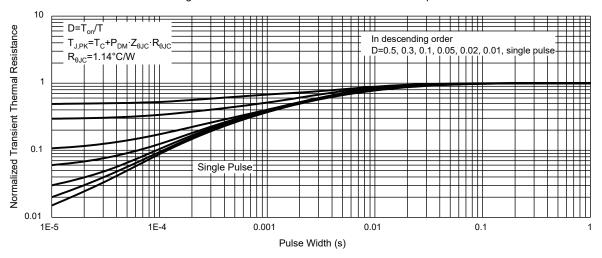


Fig. 8 - Normalized Maximum Transient Thermal Impedance





#### **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel	

Note: Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF

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